









CEP3112

30V Δ 9mΩ Δ 46A Δ Si MOSFET

SILICON Si MOSFET ▲ THT type
N-channel enhancement mode
UL94V-0 rated flame retardant epoxy
TO220-3L package

Super high dense cell density for extremely low R_{DS(ON)} **High power and current handling capability**

MAXIMUM RATINGS

Parameter (T _C = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	30V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _C = 25°C	I _D	46A
Continuous Drain Current at T _C = 100°C	I _D	32A
Pulsed Drain Current Note 1	I _{DM} Note 5	184A
Maximum Power Dissipation at T _C = 25°C	P _D	45W
Power Dissipation Derating above 25°C	ΔP_D	0.3W/°C
Single Pulsed Avalanche Energy Note 6	E _{AS}	50mJ
Single Pulsed Avalanche Current Note 6	I _{AS}	10A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

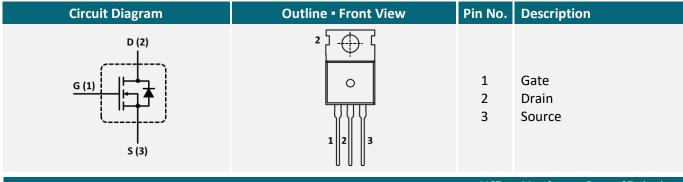
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	3.3°C/W
Thermal Resistance, Junction-to-Ambient	R _{TH JA}	62.5°C/W

APPLICATIONS

Battery Management Systems	DC/DC	High Side	Industrial	Low Side
	Converter	Switches	Control	Switches
+ 4 -				

PIN DESCRIPTION



MGT ▲ Manufacturer Group of Technology



ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V$, $V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	R _{DS(ON)}		9	12	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 4.5V$, $I_D = 10A$	R _{DS(ON)}		11	14	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		735		pF
Output Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		145		pF
Reverse Transfer Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{RSS}		110		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD} = 15V$, $V_{GS} = 10V$, $I_D = 10A$, $R_{G(ext)} = 3\Omega$	t _{D(ON)}		13		ns
Turn-On Rise Time	$V_{DD} = 15V$, $V_{GS} = 10V$, $I_D = 10A$, $R_{G(ext)} = 3\Omega$	t _R		7		ns
Turn-Off Delay Time	$V_{DD} = 15V$, $V_{GS} = 10V$, $I_D = 10A$, $R_{G(ext)} = 3\Omega$	t _{D(OFF)}		45		ns
Turn-Off Fall Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 10A, $R_{G(ext)}$ = 3 Ω	t _F		18		ns
Total Gate Charge	$V_{DS} = 15V$, $V_{GS} = 4.5V$, $I_{D} = 10A$	Q_{G}		9.3		nC
Gate Source Charge	$V_{DS} = 15V$, $V_{GS} = 4.5V$, $I_{D} = 10A$	Q_{GS}		1.8		nC
Gate Drain Charge	$V_{DS} = 15V$, $V_{GS} = 4.5V$, $I_{D} = 10A$	Q_{GD}		4.8		nC
Drain-Source Diode Characteristics an	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			34	Α
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = 1A$	V_{SD}			1.3	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Limited only by maximum temperature allowed.
- 5: Pulse width limited by safe operating area.
- 6: L = 1mH, I_{AS} = 10A, V_{DD} = 25V, R_G = 25Ω, Starting T_J = 25°C.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



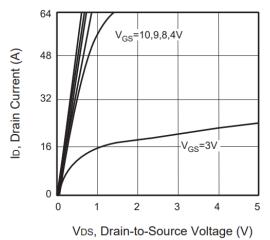


Fig. 2 • Transfer Characteristics

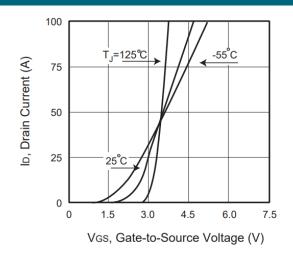


Fig. 3 • Capacitance

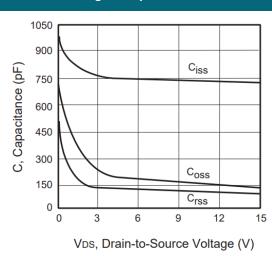


Fig. 4 • On-Resistance Variation with Temperature

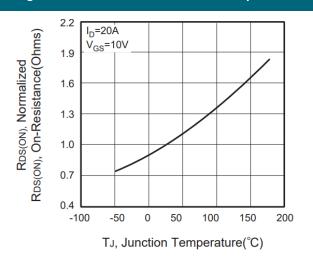


Fig. 5 • Gate Threshold Variation with Temperature

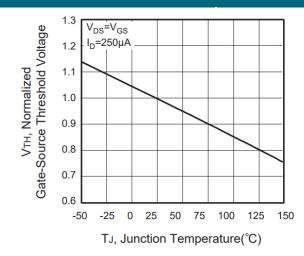
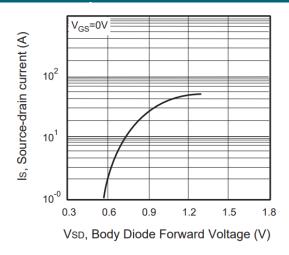


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



MGT ▲ Manufacturer Group of Technology



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

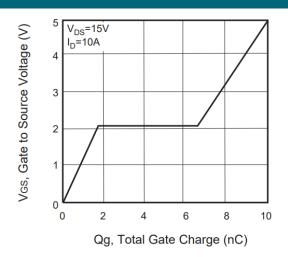


Fig. 8 • Maximum Safe Operating Area

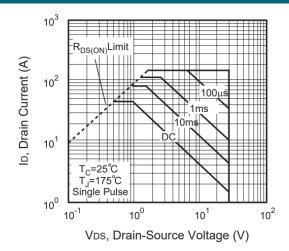
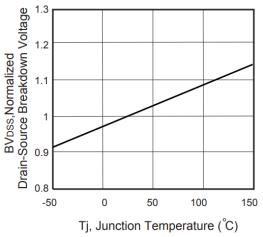


Fig. 9 • Breakdown Voltage Variation vs. Temperature





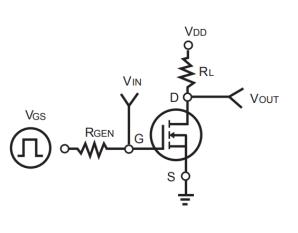
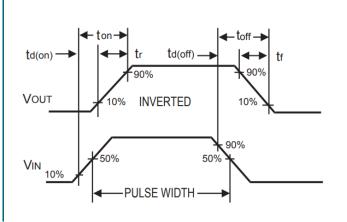


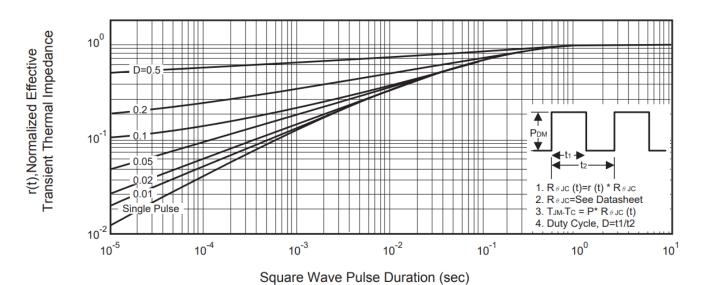
Fig. 11 • Switching Waveforms





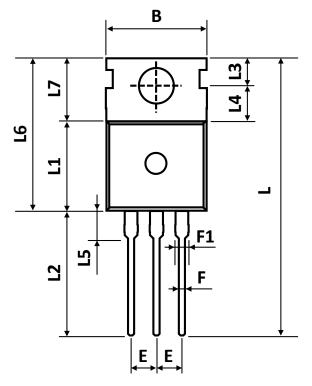
REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

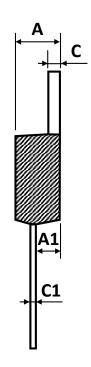
Fig. 12 • Normalized Thermal Transient Impedance Curve

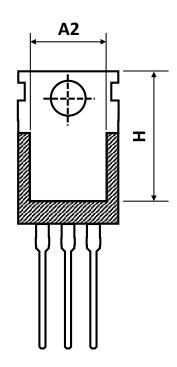




PACKAGE OUTLINE







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.43	4.53	4.63
A1	2.30	2.40	2.50
A2	7.70	7.90	8.10
В	9.80	10.00	10.20
С	1.25	1.30	1.40
C1	0.45	0.50	0.60
D	3.45	3.60	3.70
E	2.45	2.54	2.60
F	0.70	0.80	0.95
F1	1.15	1.33	1.50
L	26.80	28.80	30.80
L1	9.20	9.30	9.40
L2	12.80	13.10	13.40
L3	2.70	2.80	2.90
L4	3.50	3.70	3.80
L5	2.60	2.90	3.20
L6	15.40	15.80	16.20
L7	6.20	6.50	6.80
Н	12.95	13.25	13.55

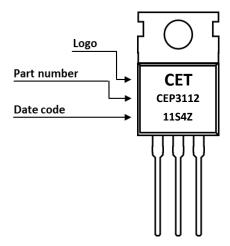
ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
CEP3112	TO-220-3L	Tube	50pcs	1,000pcs	4,000pcs

MGT ▲ Manufacturer Group of Technology

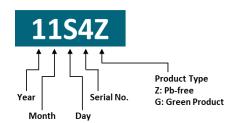


PART MARKING



DATE CODE

Example: 11S4Z



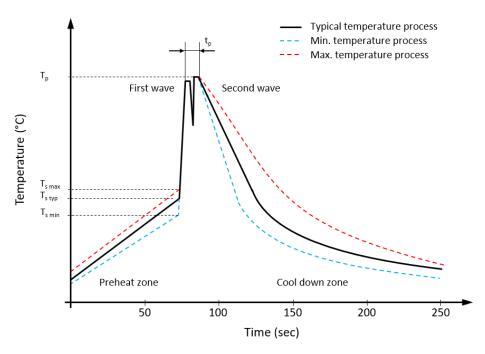


Coding list for "Day"





RECOMMENDED WAVE SOLDERING PROFILE A THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	T_{smin}	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	T_{smax}	130 °C	130 °C
Preheat time t_s from T_{smin} to T_{smax}	ts	70 seconds	70 seconds
Peak temperature	T_p	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t _p	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website www.mgt.co.com.